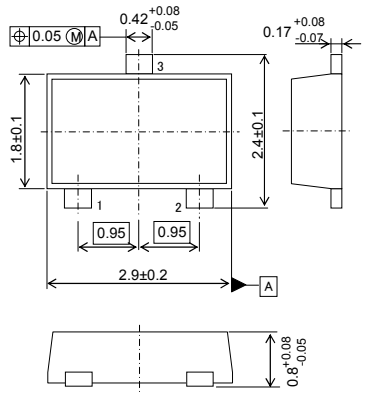
Silicon P-Channel MOS Type

Power Management Switch Applications

- 1.5-V drive
- Low ON-resistance: $R_{DS(ON)}$ = 88.4mΩ (max) (@V_{GS} = -1.5 V)
  $R_{DS(ON)}$ = 56.0mΩ (max) (@V_{GS} = -1.8 V)
  $R_{DS(ON)}$ = 39.7mΩ (max) (@V_{GS} = -2.5 V)
  $R_{DS(ON)}$ = 29.8mΩ (max) (@V_{GS} = -4.5 V)

Unit: mm



1: Gate
2: Source
3: Drain

SOT-23F

Weight: 11 mg (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	-21	V
Gate-source voltage		V_{GSS}	±8	V
Drain current	DC	I_D (Note 1)	-6.1	A
	Pulse	I_{DP} (Note 1,2)	-23.0	
Power dissipation		P_D (Note 3)	1	W
		t = 10s	2	
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

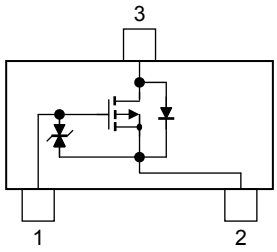
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Note 1: The channel temperature should not exceed 150°C during use.

Note 2: PW≦10μs,Duty≦1%

Note 3: Mounted on a FR4 board.
(25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 645 mm^2)

Equivalent Circuit (Top view)



Electrical Characteristics (Ta = 25°C)

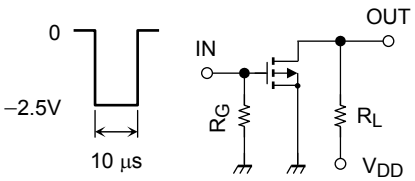
Characteristic		Symbol	Test Conditions	Min	Typ.	Max	Unit
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = -1 mA, V_{GS} = 0 V	-20	—	—	V
		$V_{(BR)\ DSX}$	I_D = -1 mA, V_{GS} = 5 V (Note 5)	-15	—	—	V
Drain cut-off current		I_{DSS}	V_{DS} = -20 V, V_{GS} = 0 V	—	—	-1	μA
Gate leakage current		I_{GSS}	V_{GS} = ±8 V, V_{DS} = 0 V	—	—	±1	μA
Gate threshold voltage		V_{th}	V_{DS} = -3 V, I_D = -1 mA	-0.3	—	-1.0	V
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = -3 V, I_D = -1.0 A (Note 4)	4.5	9.1	—	S
Drain–source ON-resistance		$R_{DS\ (ON)}$	I_D = -3.0 A, V_{GS} = -4.5 V (Note 4)	—	24.9	29.8	mΩ
			I_D = -2.5 A, V_{GS} = -2.5 V (Note 4)	—	31.1	39.7	
			I_D = -1.5 A, V_{GS} = -1.8 V (Note 4)	—	38.8	56.0	
			I_D = -0.5 A, V_{GS} = -1.5 V (Note 4)	—	47.4	88.4	
Input capacitance		C_{iss}	V_{DS} = -10 V, V_{GS} = 0 V, f = 1 MHz	—	840	—	pF
Output capacitance		C_{oss}		—	118	—	
Reverse transfer capacitance		C_{rss}		—	99	—	
Total gate charge		Q_g	V_{DD} = -10 V, I_{DS} = -4.0 A, V_{GS} = -4.5 V	—	12.8	—	nC
Gate-source charge		Q_{gs1}		—	1.4	—	
Gate-drain charge		Q_{gd}		—	3.0	—	
Switching time	Turn-on time	t_{on}	V_{DD} = -10 V, I_D = -2.0 A, V_{GS} = 0 to -2.5 V, R_G = 4.7 Ω	—	32	—	ns
	Turn-off time	t_{off}		—	107	—	
Drain-Source forward voltage		V_{DSF}	I_D = 6.0 A, V_{GS} = 0 V (Note 4)	—	0.87	1.2	V

Note4: Pulse test

Note5: V_{DSX} mode (the application of a plus voltage between gate and source) may cause decrease in maximun rating of drain-source voltage

Switching Time Test Circuit

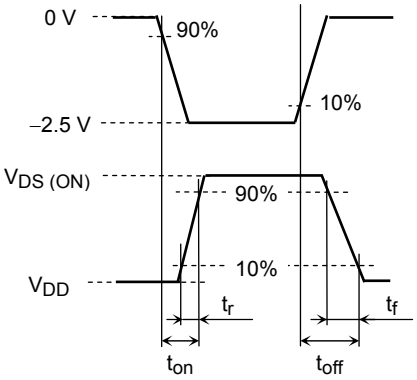
(a) Test Circuit



V_{DD} = -10 V
R_G = 4.7 Ω
Duty. ≤ 1%
V_{IN}: t_r, t_f < 5 ns
Common Source
Ta = 25°C

(b) V_{IN}

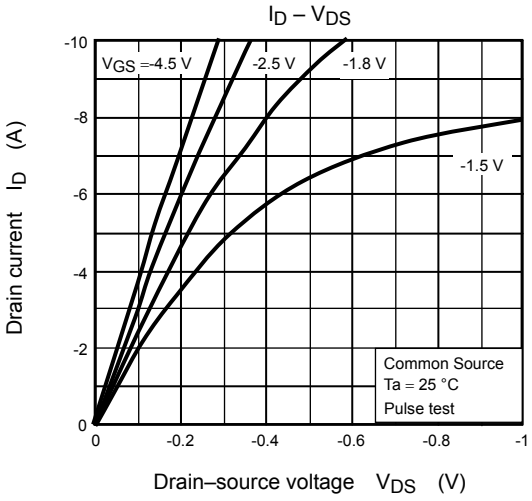
(c) V_{OUT}

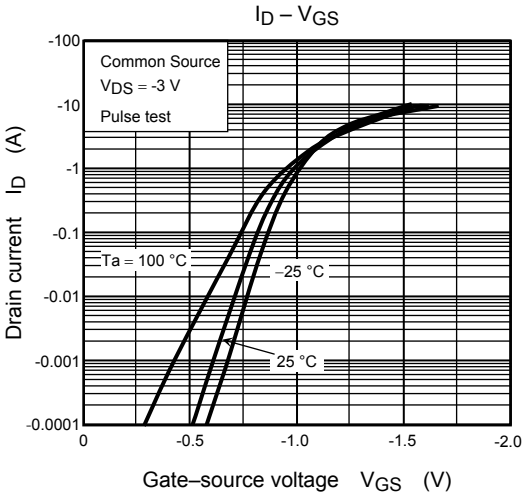


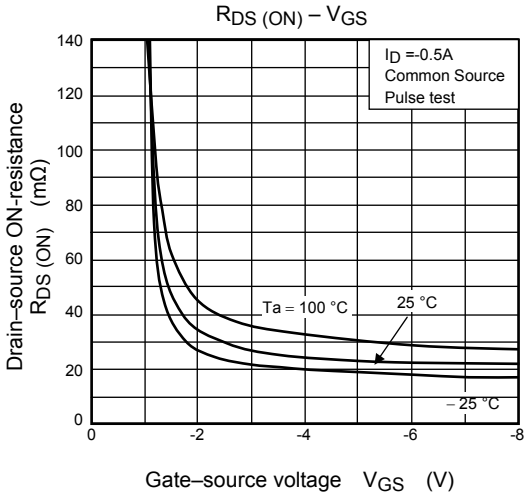
Handling Precaution

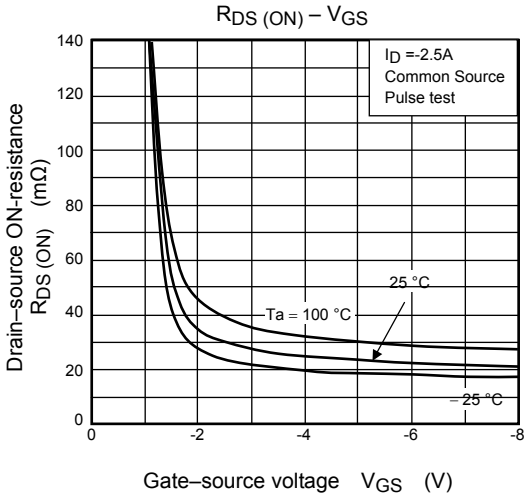
When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

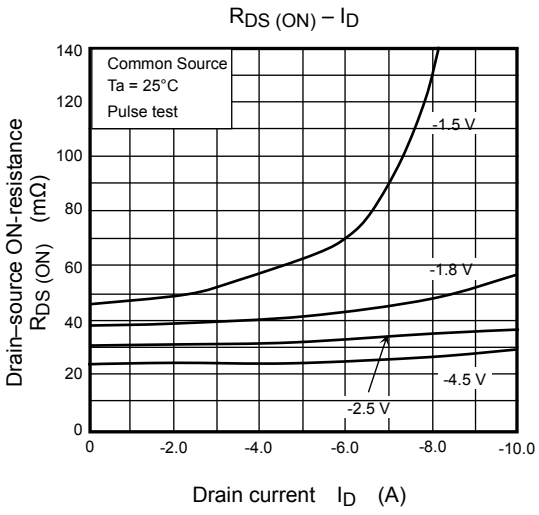
Thermal resistance $R_{th\ (ch\text{-}a)}$ and power dissipation P_D vary depending on board material, board area, board thickness and pad area. When using this device, please take heat dissipation into consideration.

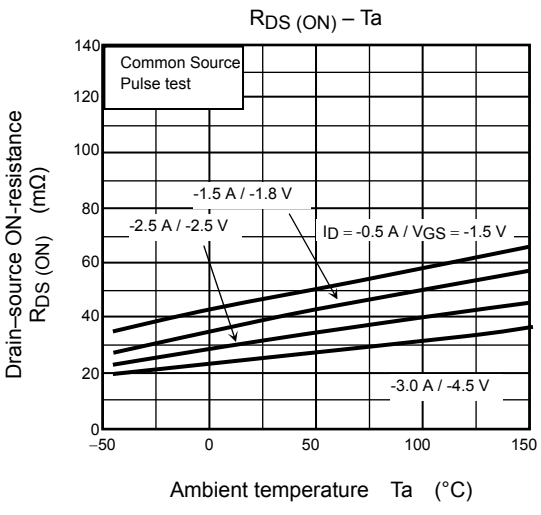

$I_D - V_{DS}$
V_{GS} =-4.5 V
-2.5 V
-1.8 V
-1.5 V
Common Source
Ta = 25 °C
Pulse test
Drain current I_D (A)
Drain–source voltage V_{DS} (V)


$I_D - V_{GS}$
Common Source
V_{DS} = -3 V
Pulse test
Ta = 100 °C
25 °C
Drain current I_D (A)
Gate–source voltage V_{GS} (V)

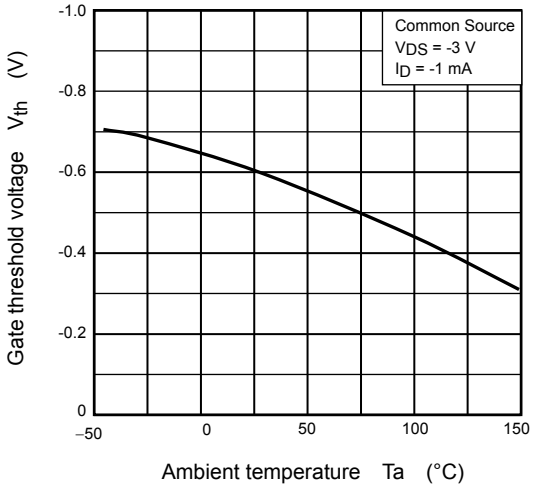

$R_{DS\ (ON)} - V_{GS}$
I_D =-0.5A
Common Source
Pulse test
Ta = 100 °C
25 °C
– 25 °C
Drain–source ON-resistance $R_{DS\ (ON)}$ (mΩ)
Gate–source voltage V_{GS} (V)


$R_{DS\ (ON)} - V_{GS}$
I_D =-2.5A
Common Source
Pulse test
Ta = 100 °C
25 °C
– 25 °C
Drain–source ON-resistance $R_{DS\ (ON)}$ (mΩ)
Gate–source voltage V_{GS} (V)

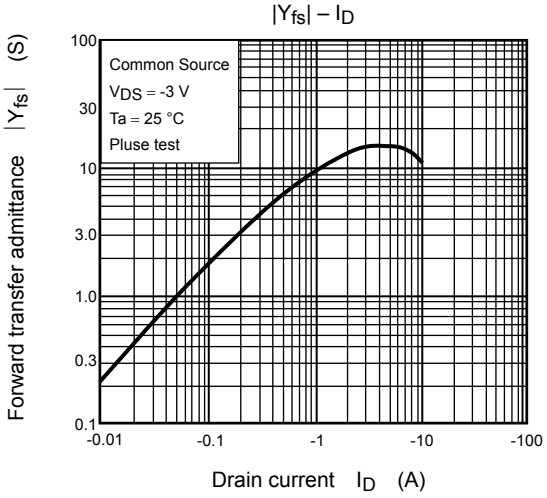

$R_{DS\ (ON)} - I_D$
Common Source
Ta = 25°C
Pulse test
-1.5 V
-1.8 V
-4.5 V
-2.5 V
Drain–source ON-resistance $R_{DS\ (ON)}$ (mΩ)
Drain current I_D (A)


$R_{DS\ (ON)} - Ta$
Common Source
Pulse test
-1.5 A / -1.8 V
-2.5 A / -2.5 V
I_D = -0.5 A / V_{GS} = -1.5 V
-3.0 A / -4.5 V
Drain–source ON-resistance $R_{DS\ (ON)}$ (mΩ)
Ambient temperature Ta (°C)

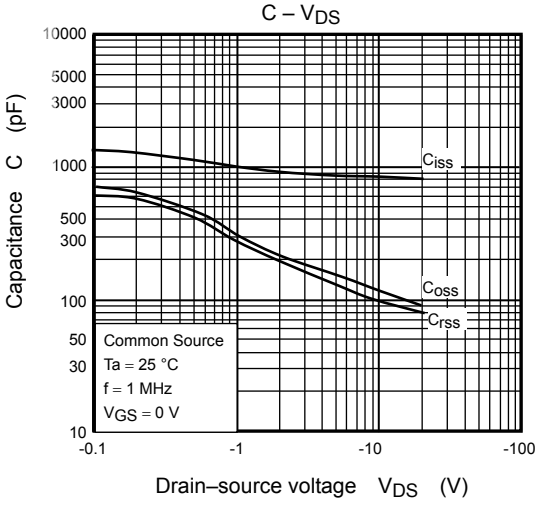
V_{th} – Ta



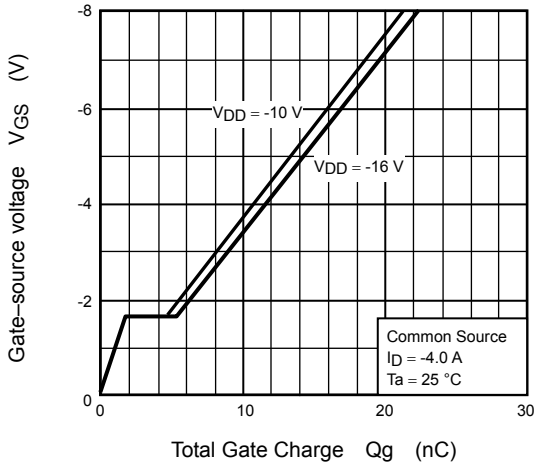
$|Y_{fs}|$ – I_D



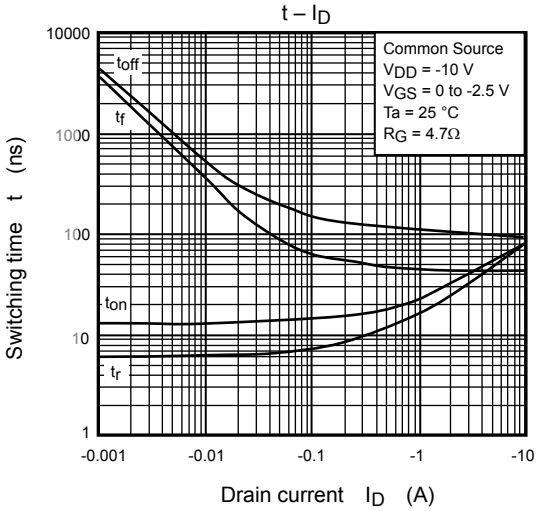
C – V_{DS}



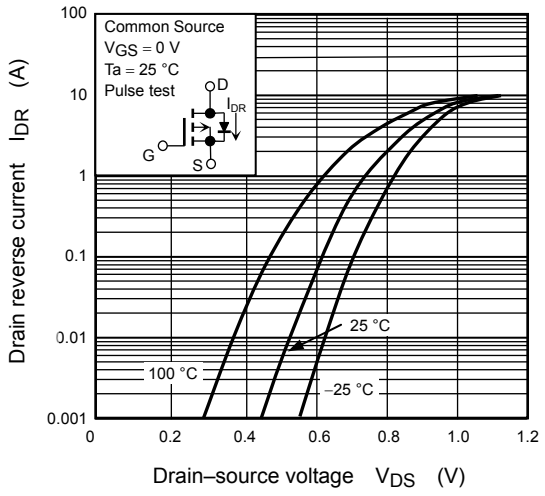
Dynamic Input Characteristic



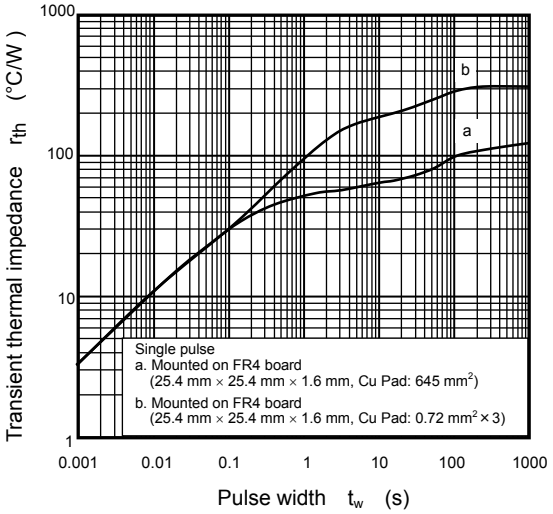
t – I_D



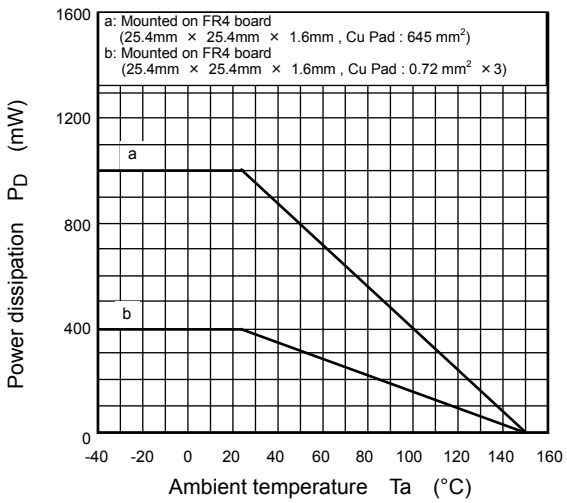
I_{DR} – V_{DS}



$r_{th} - t_w$


Transient thermal impedance rth (°C/W)
1000
100
10
1
0.001
0.01
0.1
1
10
100
1000
Pulse width tw (s)
b
a
Single pulse
a. Mounted on FR4 board
(25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 645 mm²)
b. Mounted on FR4 board
(25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 0.72 mm² × 3)

$P_D - Ta$


Power dissipation PD (mW)
1600
1200
800
400
0
-40
-20
0
20
40
60
80
100
120
140
160
Ambient temperature Ta (°C)
a
b
a: Mounted on FR4 board
(25.4mm × 25.4mm × 1.6mm , Cu Pad : 645 mm²)
b: Mounted on FR4 board
(25.4mm × 25.4mm × 1.6mm , Cu Pad : 0.72 mm² ×3)